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ZXTPS720MC

40V PNP LOW SATURATION TRANSISTOR AND 40V, 1A SCHOTTKY DIODE COMBINATION

Features and Benefits

PNP Transistor

- $BV_{CEO} > -40V$
- $I_C = -3A$ Continuous Collector Current
- Low Saturation Voltage (-220mV max @ -1A)
- $R_{SAT} = 104m\Omega$ for a low equivalent On-Resistance
- h_{FE} characterized up to -3A for high current gain hold up

Schottky Diode

- $BV_R > 40V$
- $I_{FAV} = 3A$ Average Peak Forward Current
- Low $V_F < 500mV$ (@1A) for reduced power loss
- Fast switching due to Schottky barrier
- Low profile 0.8mm high package for thin applications
- $R_{\theta JA}$ efficient, 40% lower than SOT26
- 6mm² footprint, 50% smaller than TSOP6 and SOT26
- **Lead-Free, RoHS Compliant (Note 1)**
- **Halogen and Antimony Free. "Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: DFN3020B-8
- Case Material: Molded Plastic, "Green" Molding Component
- Terminals: Pre-Plated NiPdAu leadframe
- Nominal package height: 0.8mm
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.013 grams (approximate)

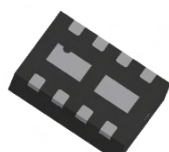
Applications

- DC – DC Converters
- Charging circuits
- Mobile phones
- Motor control
- Portable applications

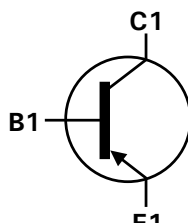
DFN3020B-8



Top View



Bottom View

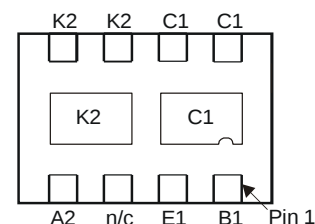


PNP Transistor



Schottky Diode

Equivalent Circuit



Bottom View
Pin-Out

n/c = Not Connected internally

Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTPS720MCTA	3S1	7	8	3000

- Notes:
1. No purposefully added lead.
 2. Diodes Inc's "Green" Policy can be found on our website <http://www.diodes.com>
 3. For packaging details, go to our website <http://www.diodes.com>

Marking Information



3S1 = Product type marking code
Top view, dot denotes pin 1

PNP - Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

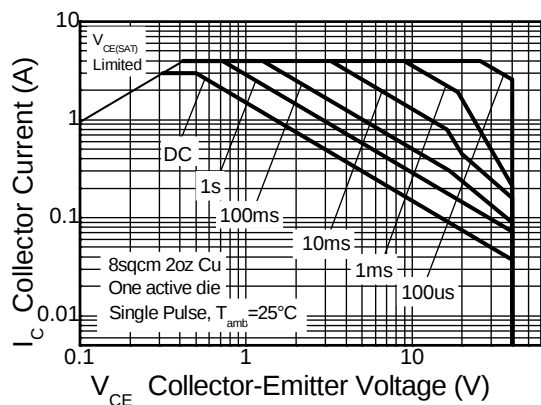
Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-40	
Emitter-Base Voltage	V_{EBO}	-7	
Peak Pulse Current	I_{CM}	-4	A
Continuous Collector Current	(Notes 4 and 7)	-3	
	(Notes 5 and 7)	-3.4	
Base Current	I_B	-1	

PNP - Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

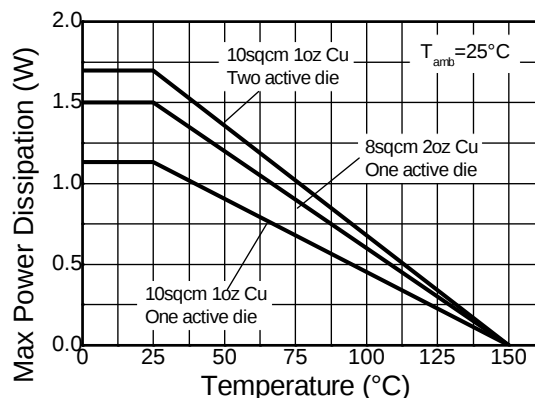
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P_D	1.5	W mW/ $^\circ\text{C}$
		12	
		2.45	
		19.6	
		1.13	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	8	$^\circ\text{C}/\text{W}$
		1.7	
		13.6	
		83.3	
		51.0	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	111	$^\circ\text{C}/\text{W}$
		73.5	
		17.1	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
4. For a dual device surface mounted on 28mm x 28mm (8cm²) FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The heatsink is split in half with the exposed collector and cathode pads connected to each half.
 5. Same as note (4), except the device is measured at $t < 5$ sec.
 6. Same as note (4), except the device is surface mounted on 31mm x 31mm (10cm²) FR4 PCB with high coverage of single sided 1oz copper.
 7. For a dual device with one active die.
 8. For dual device with 2 active die running at equal power.
 9. Thermal resistance from junction to solder-point (on the exposed collector pad).

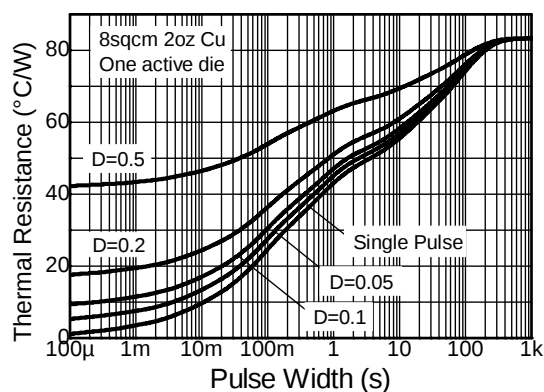
PNP - Thermal Characteristics



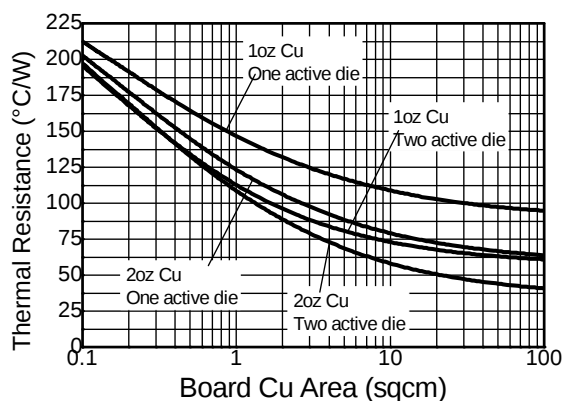
Safe Operating Area



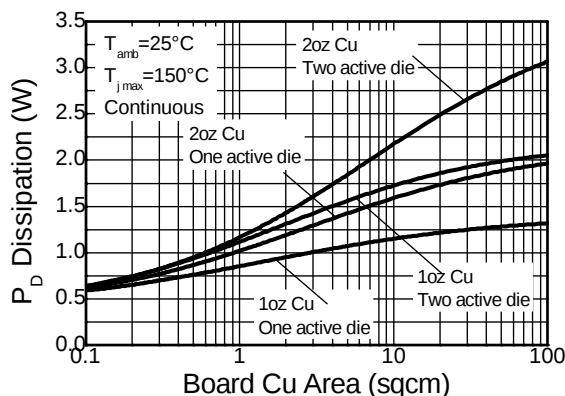
Derating Curve



Transient Thermal Impedance



Thermal Resistance v Board Area



Power Dissipation v Board Area

Schottky - Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

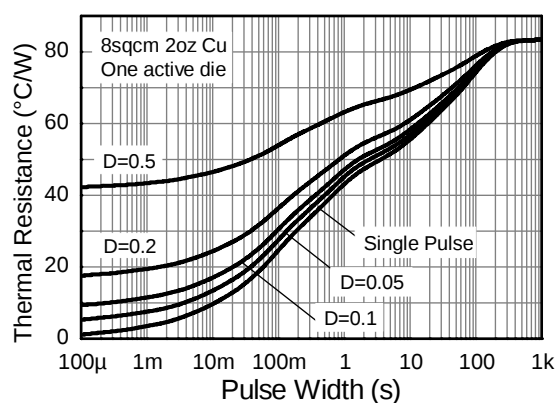
Parameter		Symbol	Limit	Unit
Continuous Reverse Voltage		V_R	40	V
Continuous Forward Current		I_F	1.85	A
Repetitive Peak Forward Current	$D = 0.5$ Pulse width $\leq 300\mu\text{s}$	I_{FRM}	3	
Non-Repetitive Peak Forward Surge Current	$t \leq 100\mu\text{s}$	I_{FSM}	12	
	$t \leq 10\text{ms}$		7	

Schottky - Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

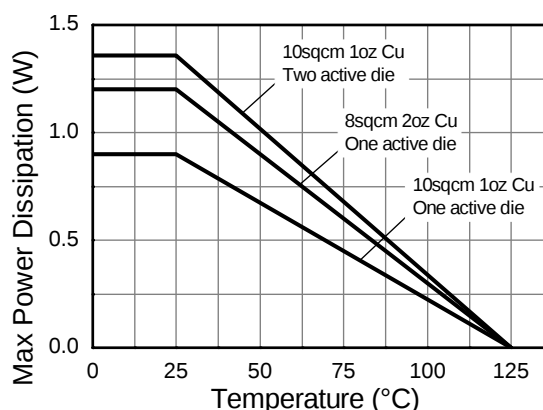
Characteristic		Symbol	Value	Unit
Power Dissipation Linear Derating Factor	(Notes 10 & 13)	P_D	1.2	W mW/ $^\circ\text{C}$
	(Notes 11 & 13)		12	
	(Notes 12 & 13)		2	
	(Notes 12 & 14)		20	
	(Notes 12 & 14)		0.9	
Thermal Resistance, Junction to Ambient	(Notes 10 & 13)	$R_{\theta JA}$	9	$^\circ\text{C}/\text{W}$
	(Notes 11 & 13)		1.36	
	(Notes 12 & 13)		13.6	
	(Notes 12 & 14)		83.3	
Thermal Resistance, Junction to Lead	(Note 15)	$R_{\theta JL}$	51.0	$^\circ\text{C}$
Storage Temperature Range		T_{STG}	111	
Maximum Junction Temperature		T_J	-55 to +150	$^\circ\text{C}$

- Notes:
- For a dual device surface mounted on 28mm x 28mm (8cm²) FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The heatsink is split in half with the exposed cathode and collector pads connected to each half.
 - Same as note (10), except the device is measured at $t < 5$ sec.
 - Same as note (10), except the device is surface mounted on 31mm x 31mm (10cm²) FR4 PCB with high coverage of single sided 1oz copper.
 - For a dual device with one active die.
 - For dual device with 2 active die running at equal power.
 - Thermal resistance from junction to solder-point (on the exposed cathode pad).

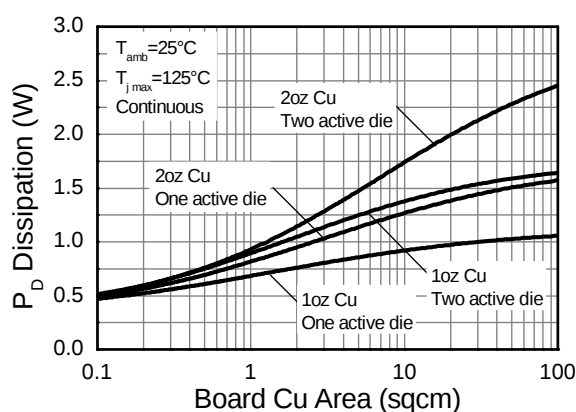
Schottky - Thermal Characteristics



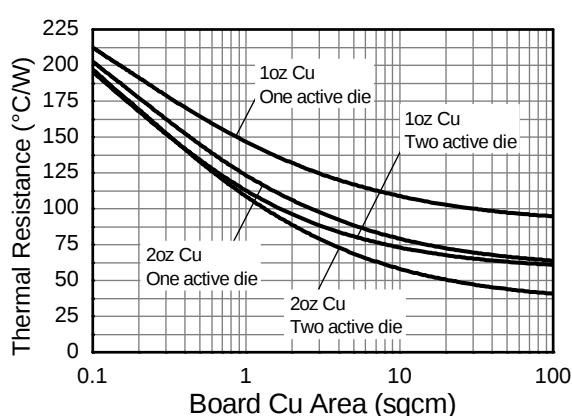
Transient Thermal Impedance



Derating Curve



Power Dissipation v Board Area



Thermal Resistance v Board Area

PNP - Electrical Characteristics @T_A = 25°C unless otherwise specified

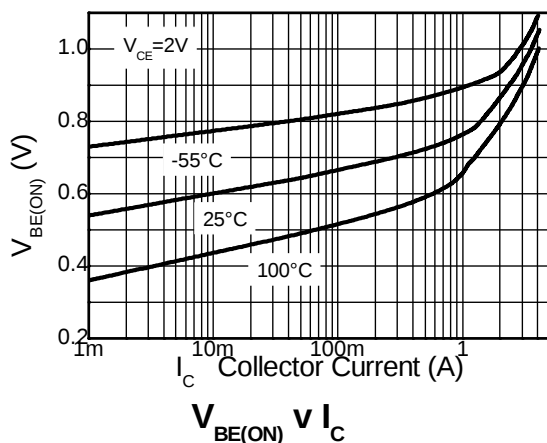
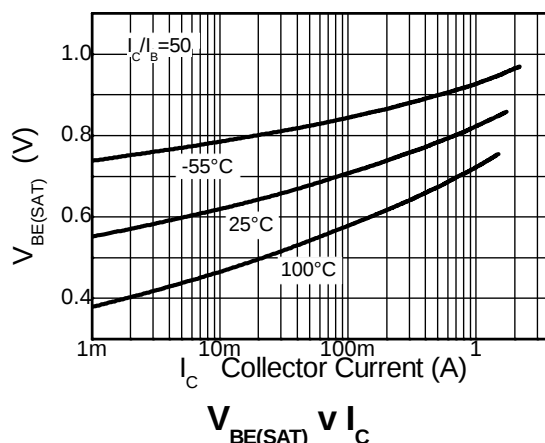
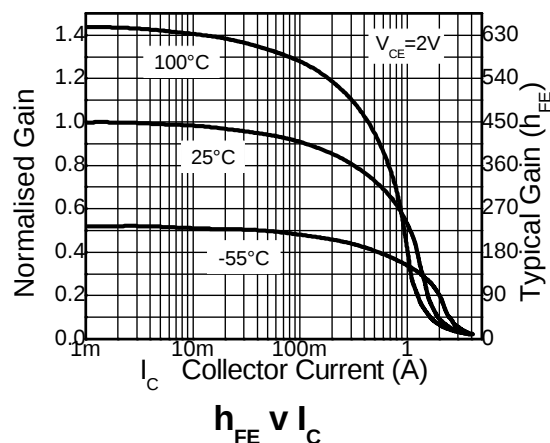
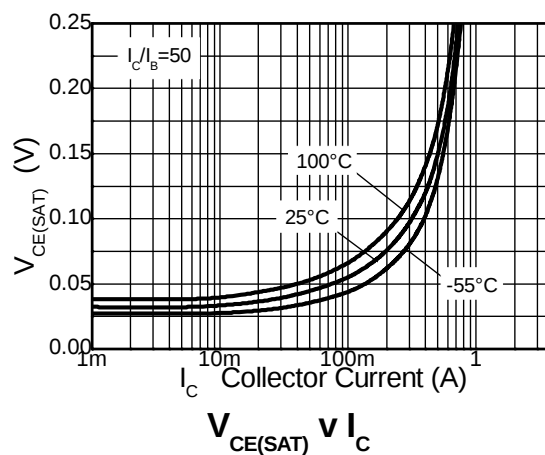
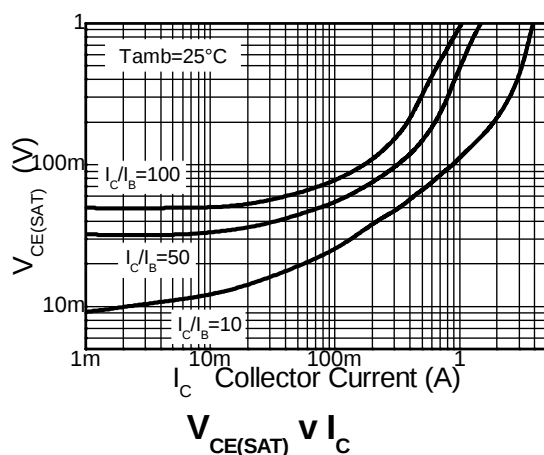
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-50	-80	-	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 16)	BV _{CEO}	-40	-70	-	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.5	-	V	I _E = -100μA
Collector Cutoff Current	I _{CBO}	-	-	-100	nA	V _{CB} = -40V
Emitter Cutoff Current	I _{EBO}	-	-	-100	nA	V _{EB} = -6V
Collector Emitter Cutoff Current	I _{CES}	-	-	-100	nA	V _{CES} = -32V
Static Forward Current Transfer Ratio (Note 16)	h _{FE}	300	480	-	-	I _C = -10mA, V _{CE} = -2V
		300	450	-		I _C = -100mA, V _{CE} = -2V
		180	290	-		I _C = -1A, V _{CE} = -2V
		60	130	-		I _C = -1.5A, V _{CE} = -2V
		12	22	-		I _C = -3A, V _{CE} = -2V
Collector-Emitter Saturation Voltage (Note 16)	V _{CE(sat)}	-	-25	-40	mV	I _C = -0.1A, I _B = -10mA
		-	-150	-220		I _C = -1A, I _B = -50mA
		-	-195	-300		I _C = -1.5A, I _B = -100mA
		-	-210	-300		I _C = -2A, I _B = -200mA
		-	-260	-370		I _C = -2.5A, I _B = -250mA
Base-Emitter Turn-On Voltage (Note 16)	V _{BE(on)}	-	-0.89	-0.95	V	I _C = -2.5A, V _{CE} = -2V
Base-Emitter Saturation Voltage (Note 16)	V _{BE(sat)}	-	-0.97	-1.05	V	I _C = -2.5A, I _B = -250mA
Output Capacitance	C _{obo}	-	19	25	pF	V _{CB} = -10V, f = 1MHz
Transition Frequency	f _T	150	190	-	MHz	V _{CE} = -10V, I _C = -50mA, f = 100MHz
Turn-on Time	t _{on}	-	40	-	ns	V _{CC} = -15V, I _C = -0.75A
Turn-off Time	t _{off}	-	435	-	ns	I _{B1} = I _{B2} = -15mA

Schottky - Electrical Characteristics @T_A = 25°C unless otherwise specified

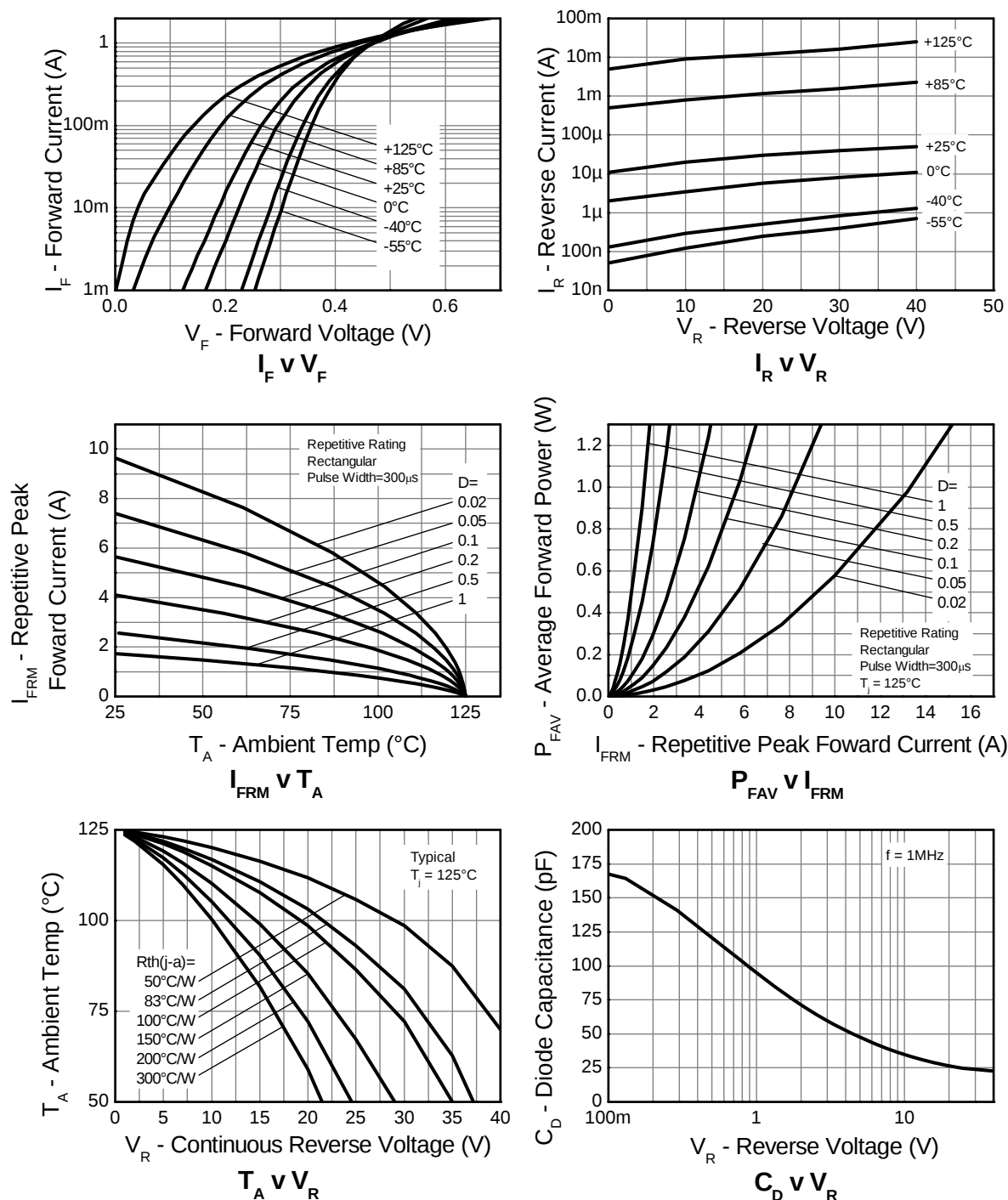
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Breakdown Voltage	BV _R	40	60	-	V	I _R = -300μA
Forward Voltage (Note 16)	V _F	-	240	270	mV	I _F = 50mA
		-	265	290		I _F = 100mA
		-	305	340		I _F = 250mA
		-	355	400		I _F = 500mA
		-	390	450		I _F = 750mA
		-	425	500		I _F = 1000mA
		-	495	600		I _F = 1500mA
		-	420	-		I _F = 1000mA, T _A = 100°C
Reverse Current	I _R	-	50	100	μA	V _R = 30V
Diode Capacitance	C _D	-	25	-	pF	V _R = 25V, f = 1MHz
Reverse Recovery Time	t _{rr}	-	12	-	ns	switched from I _F = 500mA to I _R = 500mA Measured at I _R = 50mA

Notes: 16. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

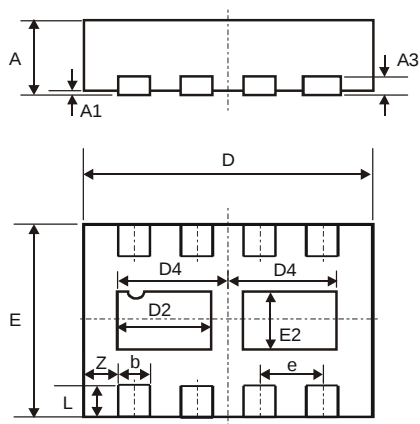
PNP - Typical Electrical Characteristics



Schottky - Typical Electrical Characteristics

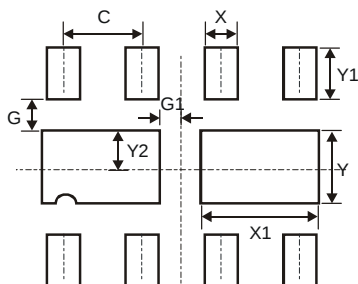


Package Outline Dimensions



DFN3020B-8			
Dim	Min	Max	Typ
A	0.77	0.83	0.80
A1	0	0.05	0.02
A3	-	-	0.15
b	0.25	0.35	0.30
D	2.95	3.075	3.00
D2	0.82	1.02	0.92
D4	1.01	1.21	1.11
e	-	-	0.65
E	1.95	2.075	2.00
E2	0.43	0.63	0.53
L	0.25	0.35	0.30
Z	-	-	0.375
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.650
G	0.285
G1	0.090
X	0.400
X1	1.120
Y	0.730
Y1	0.500
Y2	0.365

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